Lecture 25 Multistage Amplifiers (II) DC VOLTAGE AND CURRENT SOURCES

Outline

- 1. DC Voltage Sources
- 2. DC Current Sources and Sinks

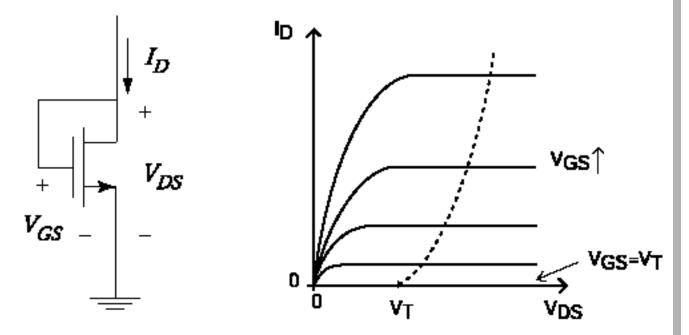
Reading Assignment: Howe and Sodini, Chapter 9, Sections 9-3-9.4

1. DC Voltage Sources

Characteristics of DC Voltage Sources :

- A well controlled output voltage
- Output voltage does not depend on current drawn from source ⇒ *Low Thevenin Resistance*

Consider a MOSFET connected in "diode configuration"



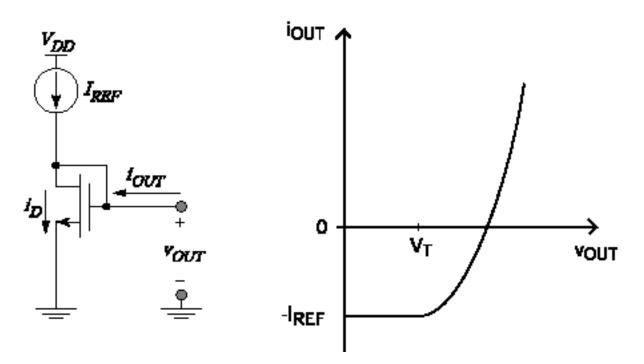
I-V characteristics:

$$\mathbf{I}_{\mathbf{D}} = \frac{\mathbf{W}}{2\mathbf{L}} \boldsymbol{\mu}_{\mathbf{n}} \mathbf{C}_{\mathbf{ox}} (\mathbf{V}_{\mathbf{GS}} - \mathbf{V}_{\mathbf{Tn}})^2 = \frac{\mathbf{W}}{2\mathbf{L}} \boldsymbol{\mu}_{\mathbf{n}} \mathbf{C}_{\mathbf{ox}} (\mathbf{V}_{\mathbf{DS}} - \mathbf{V}_{\mathbf{Tn}})^2$$

Beyond the threshold voltage, the MOSFET looks like a "diode" with quadratic I-V characteristics

How does one synthesize a voltage source with this?

Assume a current source is available



 $V_{GS} = V_{DS} \text{ takes a value needed to sink current}$ $i_D = I_{REF} + i_{OUT} = \frac{W}{2L} \mu_n C_{ox} (v_{OUT} - V_{Tn})^2$

Then:

$$i_{OUT} = \frac{W}{2L} \mu_n C_{ox} \left(v_{OUT} - V_{Tn} \right)^2 - I_{REF}$$

Solving for v_{OUT}:

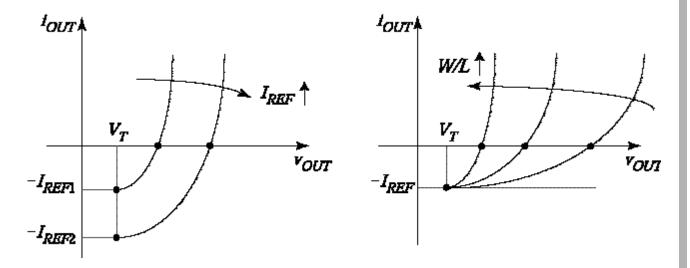
$$v_{OUT} = V_{Tn} + \sqrt{\frac{I_{REF} + i_{OUT}}{\frac{W}{2L}} \mu_n C_{ox}}$$

Synthesizing Voltage Sources (contd.)

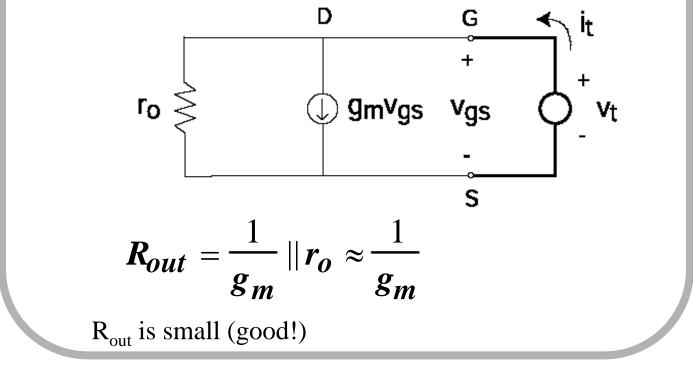
 v_{OUT} is a function of I_{REF} and W/L of MOSFET:

•
$$I_{\text{REF}} \uparrow \Rightarrow v_{\text{OUT}} \uparrow$$

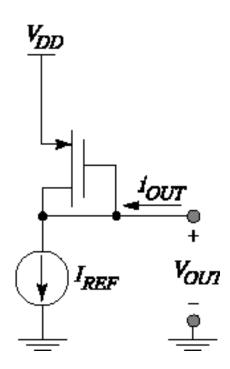
• W/L
$$\uparrow \Rightarrow v_{OUT} \downarrow$$



Small Signal Equivalent Circuit Model:



PMOS voltage source



Same operation and characteristics as NMOS voltage source. PMOS needs to be larger to attain the same R_{out} .

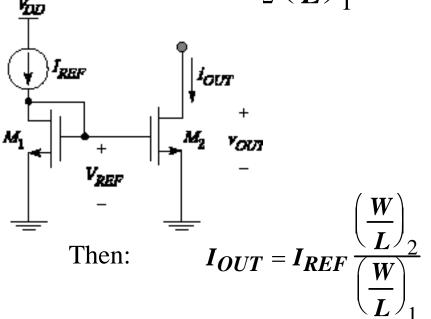
3. DC Current Sources and Sinks

Characteristics of Current Sources

- A well controlled output current
- Supplied current does not depend on output voltage ⇒ *High Norton Resistance*

Connect a voltage source to the gate of another MOSFET:

$$I_{OUT} \approx \frac{1}{2} \left(\frac{W}{L} \right)_2 \mu_n C_{ox} \left(V_{REF} - V_{Tn} \right)^2$$
$$I_{REF} \approx \frac{1}{2} \left(\frac{W}{L} \right)_1 \mu_n C_{ox} \left(V_{REF} - V_{Tn} \right)^2$$

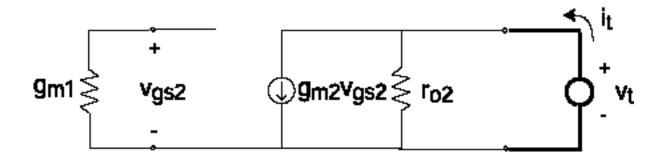


 I_{OUT} scales with I_{REF} by W/L ratios of two MOSFETs \Rightarrow *Current Mirror Circuit*

Well "matched" transistors important.

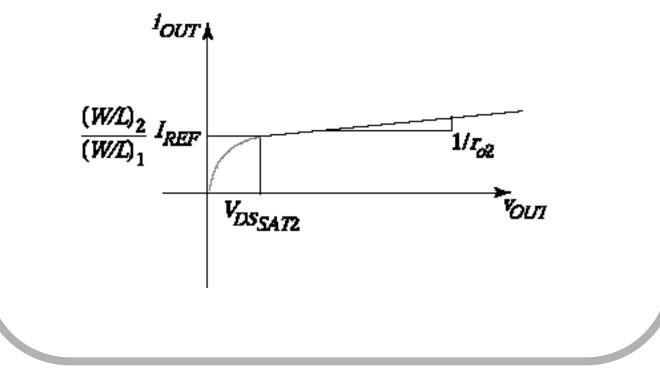
DC Current Sources and Sinks (contd.)

Small Signal Equivalent Circuit Model:



 $R_{out 2} = r_{o 2}$

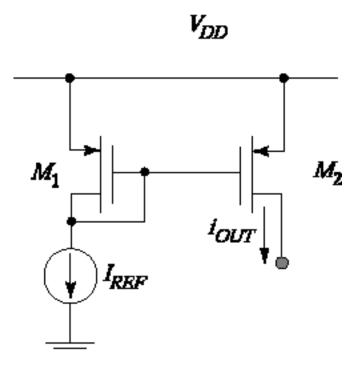
I-V characteristics of NMOS current source:



PMOS Current Source

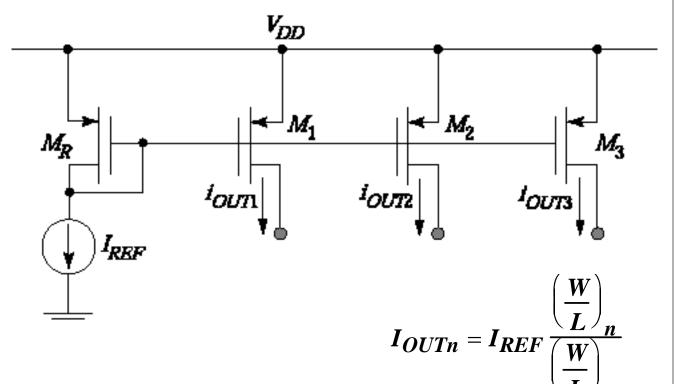
- NMOS current source sinks current to ground
- PMOS current source sources current from positive supply

PMOS Current Mirror:

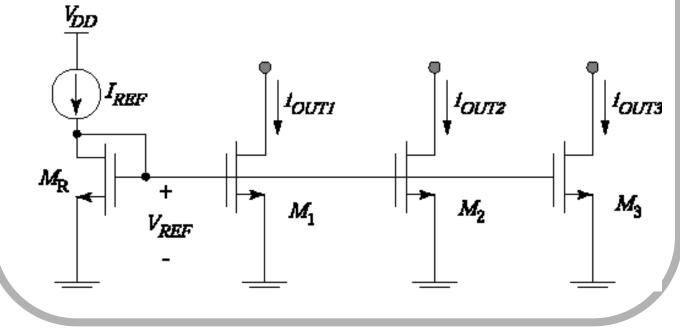


3. Multiple Current Sources

Since there is no DC gate current in MOSFET, we can tie up multiple current mirrors to single current source:



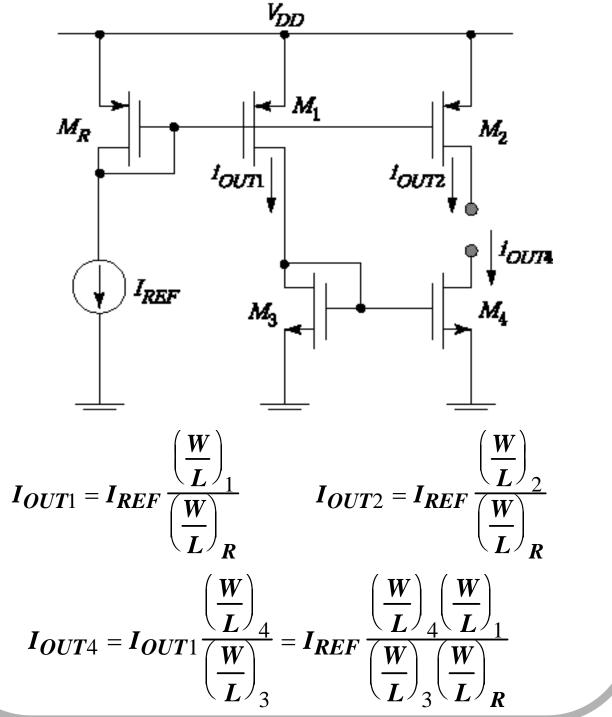
Similar idea with NMOS current sinks:



R

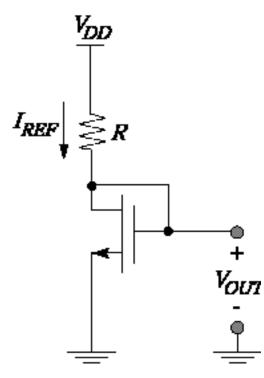
Multiple Current Sources and Sinks

Often, in a given circuit, we need current sources and sinks. We can build them all out of a single current source.



Generating I_{REF}

Simple circuit:



$$I_{REF} = \frac{V_{DD} - V_{OUT}}{R}$$

$$V_{OUT} = V_{Tn} + \sqrt{\frac{I_{REF}}{\frac{W}{2L}\mu_n C_{ox}}}$$

For large W/L:

$$I_{REF} \approx rac{V_{DD} - V_{Tn}}{R}$$

- Advantages
 - I_{REF} set by value of resistor
- Disadvantages
 - V_{DD} also affects I_{REF}.
 - V_{Tn} and R are functions of temperature $\Rightarrow I_{REF}(T)$.

In the real world, more sophisticated circuits are used to generate I_{REF} that are V_{DD} and T independent.

What did we learn today?

Summary of Key Concepts

- *Voltage source* easily synthesized from **reference** *current source* using MOSFET in diode configuration
- *Current source* easily synthesized from *current source* using current mirror circuit.
- Multiple current sources and sinks with different magnitudes can be synthesized from a single current source.
- Voltage and current sources rely on the availability of well "matched" transistors in IC technology.